

**AMENDMENTS TO THE CLAIMS**

Please amend the claims as follows:

Claim 1. (currently amended) A process of preparing a semiconductive film comprising:

applying a solution containing a soluble polymer and a soluble metal precursor onto a substrate to form a layer containing said polymer and said metal ~~precursor~~containing layer thereon;

treating said substrate including said ~~layer~~polymer and metal containing layer for a time to form a coherent composite film;

heating said substrate in an oxygen-containing atmosphere at temperatures characterized as sufficient to remove said polymer from said composite film and form a metal oxide film; and,

reacting said metal oxide film with a sulfur-, selenium- or tellurium-containing gas under conditions sufficient to form a semiconductive film.

Claim 2. (original) The process of claim 1 wherein said solution is an aqueous solution having a pH of from about 4 to about 7.

Claim 3. (original) The process of claim 1 wherein said semiconductive film contains a single metal selected from the group consisting of cadmium, indium, zinc, copper and titanium.

Claim 4. (original) The process of claim 1 wherein said metal oxide film is cadmium oxide and said semiconductive film is selected from the group consisting of cadmium sulfide, cadmium selenide, cadmium telluride or mixtures thereof.

Claim 5. (currently amended) The process of claim 2 wherein said aqueous solution in said process is organic-solvent free.

Claim 6. (cancelled)

Claim 7. (cancelled)

Claim 8. (original) The process of claim 1 wherein said metal oxide film is a mixed metal oxide selected from the group consisting of zinc and cadmium, copper and indium, copper and gallium, cadmium and indium, and copper, gallium and indium.

Claim 9. (original) The process of claim 8 wherein said semiconductive film is selected from the group consisting of zinc cadmium sulfide, zinc cadmium selenide, zinc cadmium telluride or mixtures thereof.

Claim 10. (cancelled)

Claim 11. (original) The process of claim 8 wherein said semiconductive film is selected from the group consisting of cadmium indium sulfide, cadmium indium selenide, cadmium indium telluride or mixtures thereof.

Claim 12. (cancelled)

Claim 13. (cancelled)

Claim 14. (original) The process of claim 1 wherein said soluble polymer is selected from the group consisting of poly(vinyl alcohol), polyethylene glycol, poly(acrylic acid), poly(diallyldimethyl ammonium chloride), and polyethylenimine.

Claim 15. (original) The process of claim 1 wherein said soluble polymer is polyvinyl alcohol.

Claim 16. (cancelled)

Claim 17. (original) The process of claim 1 wherein said treating includes drying at temperatures characterized as insufficient to remove said polymer but sufficient to form the coherent composite film.

Claim 18. (cancelled)

Claim 19. (cancelled)

Claim 20. (cancelled)